

8755A

16,384-Bit EPROM with I/O

The Intel 8755A is an erasable and electrically reprogrammable ROM (EPROM) and I/O chip to be used in the 8085AH microprocessor systems. The EPROM portion is organized as 2048 words by 8 bits. It has a maximum access time of 450 ns to permit use with no wait states in an 8085AH CPU. The I/O portion consists of 2 general purpose I/O ports. Each I/O port has 8 port lines, and each I/O port line is individually programmable as input or output.

Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceeds the OCM data sheet.

Quality Overview

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-38535
 - Class Q Military
 - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
 - Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

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8755A 16,384-BIT EPROM WITH I/O

- 2048 Words x 8 Bits
- Single + 5V Power Supply (V_{CC})
- Directly Compatible with 8085AH
- U.V. Erasable and Electrically Reprogrammable
- Internal Address Latch

- 2 General Purpose 8-Bit I/O Ports
- Each I/O Port Line Individually Programmable as Input or Output
- Multiplexed Address and Data Bus
- 40-Pin DIP
- Available in EXPRESS
 Standard Temperature Range
 - Extended Temperature Range

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Figure 2. Pin Configuration

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Table 1. Pin Description

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Symbol	Туре	Name and Function
ALE		ADDRESS LATCH ENABLE: When Address Latch Enable goes <i>high</i> , AD_{0-7} , IO/\overline{M} , A_{8-10} , CE_2 , and $\overline{CE_1}$ enter the address latches. The signals, (AD, IO/M, AD_{8-10} , CE_2 , $\overline{CE_1}$) are latched in at the trailing edge of ALE.
AD ₀₋₇	I	BIDIRECTIONAL ADDRESS/DATA BUS: The lower 8 bits of the PROM or I/O address are applied to the bus lines when ALE is high. During an I/O cycle, Port A or B is selected based on the latched value of AD _O . IF RD or IOR is low when the latched Chip Enables are active, the output buffers present data on the bus.
AD ₈₋₁₀	I	ADDRESS BUS: These are the high order bits of the PROM address. They do not affect I/O operations.
PROG/CE ₁ CE ₂	I	CHIP ENABLE INPUTS: CE_1 is active low and CE_2 is active high. The 8755A can be accessed only when <i>both</i> Chip Enables are active at the time the ALE signal latches them up. If either Chip Enable input is not active, the AD_{0-7} , and READY ouputs will be in a high impedance state. $\overline{CE_1}$ is also used as a programming pin. (See section on programming.)
10/ M	1	I/O MEMORY: If the latched IO/\overline{M} is high when \overline{RD} is low, the output data comes from an I/O port. If it is low the output data comes from the PROM.
RD	I	READ: If the latched Chip Enables are active when RD goes low, the AD_{0-7} output buffers are enabled and output either the selected PROM location or I/O port. When both RD and IOR are high, the AD_{0-7} output buffers are 3-stated.
IOW		I/O WRITE: If the latched Chip Enables are active, a low on \overline{IOW} causes the output port pointed to by the latched value of AD_0 to be written with the data on AD_{0-7} . The state of IO/\overline{M} is ignored.
CLK	I	CLOCK: The CLK is used to force the READY into its high impedance state after it has been forced low by $\overline{CE_1}$ low, CE_2 high, and ALE high.
READY	0	READY is a 3-state output controlled by $\overline{CE_1}$, CE_2 , ALE and CLK. READY is forced low when the Chip Enables are active during the time ALE is high, and remains low until the rising edge of the next CLK. (See Figure 6c.)
PA ₀₋₇	1/0	PORT A: These are general purpose I/O pins. Their input/output direction is determined by the contents of Data Direction Register (DDR). Port A is selected for write operations when the Chip Enables are active and \overline{IOW} is low and a 0 was previously latched from AD_0 , AD_1 . Read Operation is selected by either \overline{IOR} low and active Chip Enables and AD_0 and AD_1 low, <i>or</i> IO/\overline{M} high, \overline{RD} low, active Chip Enables, and AD_0 and AD_1 low.
PB ₀₋₇	1/0	PORT B: The general purpose I/O port is identical to Port A except that it is selected by a 1 latched from AD_0 and a 0 from AD_1 .
RESET	ł	RESET: In normal operation, an input high on RESET causes all pins in Ports A and B to assume input mode (clear DDR register).
IOR	I	I/O READ: When the Chip Enables are active, a low on \overline{IOR} will output the selected I/O port onto the AD bus. \overline{IOR} low performs the same function as the combination of IO/M high and RD low. When \overline{IOR} is not used in a system, \overline{IOR} should be tied to V_{CC} ("1").
Vcc		POWER: + 5V supply.
V _{SS}		GROUND: Reference.
V _{DD}		POWER SUPPLY: V_{DD} is a programming voltage, and must be tied to V_{CC} when the 8755A is being read. For programming, a high voltage is supplied with $V_{DD} = 25V$, typical. (See section on programming.)

FUNCTIONAL DESCRIPTION

PROM Section

The 8755A contains an 8-bit address latch which allows it to interface directly to MCS®-48 and MCS®-85 processors without additional hardware.

The PROM section of the chip is addressed by the 11-bit address and the Chip Enables. The address, $\overline{CE_1}$ and CE_2 are latched into the address latches on the falling edge of ALE. If the latched Chip Enables are active and IO/M is low when RD goes low, the contents of the PROM location addressed by the latched address are put out on the AD₀₋₇ lines (provided that V_{DD} is tied to V_{CC}).

I/O Section

The I/O section of the chip is addressed by the latched value of AD_{0-1} . Two 8-bit Data Direction Registers (DDR) in 8755A determine the input/output status of each pin in the corresponding ports. A "0" in a particular bit position of a DDR signifies that the corresponding I/O port bit is in the input mode. A "1" in a particular bit position signifies that the corresponding I/O port bit is in the output mode. In this manner the I/O ports of the 8755A are bit-by-bit programmable as inputs or outputs. The table summarizes port and DDR designation. DDR's cannot be read.

AD1	AD ₀	Selection
0	0	Port A
0	1	Port B
1	0	Port A Data Direction Register (DDR A)
1	1	Port B Data Direction Register (DDR B)

When \overline{IOW} goes low and the Chip Enables are active, the data on the AD_{0-7} is written into I/O port selected by the latched value of AD_{0-1} . During this operation all I/O bits of the selected port are affected, regardless of their I/O mode and the state of IO/ \overline{M} . The actual output level does not change until \overline{IOW} returns high. (Glitch free output.) A port can be read out when the latched Chip Enables are active and either \overline{RD} goes low with IO/\overline{M} high, or \overline{IOR} goes low. Both input and output mode bits of a selected port will appear on lines AD_{0-7} .

To clarify the function of the I/O Ports and Data Direction Registers, the following diagram shows the configuration of one bit of PORT A and DDR A. The same logic applies to PORT B and DDR B.





Note that hardware RESET or writing a zero to the DDR latch will cause the output latch's output buffer to be disabled, preventing the data in the Output Latch from being passed through to the pin. This is equivalent to putting the port in the input mode. Note also that the data can be written to the Output Latch even though the Output Buffer has been disabled. This enables a port to be initialized with a value prior to enabling the output.

The diagram also shows that the contents of PORT A and PORT B can be read even when the ports are configured as outputs.

ERASURE CHARACTERISTICS

The erasure characteristics of the 8755A are such that erasure begins to occur when exposed to light with wavelengths shorter than approximately 4000 Angstroms (Å). It should be noted that sunlight and certain types of fluorescent lamps have wavelengths in the 3000-4000Å range. Data show that constant exposure to room level fluorescent lighting could erase the typical 8755A in approximately 3 years while it would take approximately 1 week to cause erasure when exposed to direct sunlight. If the 8755A is to be exposed to these types of lighting conditions for extended periods of time, opaque labels are available from Intel which should be placed over the 8755A window to prevent unintentional erasure.

The recommended erasure procedure for the 8755A is exposure to shortwave ultraviolet light which has a wavelength of 2537 Angstroms (Å). The integrated dose (i.e., UV intensity x exposure time) for erasure should be a minimum of 15W-sec/cm². The erasure time with this dosage is approximately 15 to 20 minutes using an ultraviolet lamp with a 12000 μ W/cm² power rating. The 8755A should be placed within one inch from the lamp tubes during erasure. Some lamps have a filter on their tubes and this filter should be removed before erasure.

PROGRAMMING

Initially, and after each erasure, all bits of the EPROM portions of the 8755A are in the "1" state. Information is introduced by selectively programming "0" into the desired bit locations. A programmed "0" can only be changed to a "1" by UV erasure.

The 8755A can be programmed on the Intel Universal Programmer (iUP), and iUPF8744A programming module.

The program mode itself consists of programming a single address at a time, giving a single 50 msec pulse for every address. Generally, it is desirable to have a verify cycle after a program cycle for the same address as shown in the attached timing diagram. In the verify cycle (i.e., normal memory read cycle) 'V_{DD}' should be at + 5V.

SYSTEM APPLICATIONS

System Interface with 8085AH

A system using the 8755A can use either one of the two I/O Interface techniques:

- Standard I/O
- Memory Mapped I/O

If a standard I/O technique is used, the system can use the feature of both CE₂ and CE₁. By using a combination of unused address lines A_{11-15} and the Chip Enable inputs, the 8085AH system can use up to 5 8755A's without requiring a CE decoder. See Figure 4.

If a memory mapped I/O approach is used the 8755A will be selected by the combination of both the Chip Enables and IO/\overline{M} using AD_{8-15} address lines. See Figure 3.



Figure 3. 8755A in 8085AH System (Memory-Mapped I/O)



Figure 4. 8755A in 8085AH System (Standard I/O)

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ABSOLUTE MAXIMUM RATINGS*

Temperature Under Bias	.0°C to +70°C
Storage Temperature68	5°C to + 150°C
Voltage on any Pin with Respect to Ground	-0.5V to +7V
Power Dissipation	1.5W

NOTICE: This is a production data sheet. The specifications are subject to change without notice.

*WARNING: Stressing the device beyond the "Absolute Maximum Ratings" may cause permanent damage. These are stress ratings only. Operation beyond the "Operating Conditions" is not recommended and extended exposure beyond the "Operating Conditions" may affect device reliability.

D.C. CHARACTERISTICS

 $T_A = 0^{\circ}C$ to 70°C, $V_{CC} = V_{DD} = 5V \pm 5\%$

Symbol	Parameter	Min	Max	Unit	Test Conditions
VIL	Input Low Voltage	-0.5	0.8	v	$V_{\rm CC} = 5.0 V$
VIH	Input High Voltage	2.0	V _{CC} + 0.5	v	$V_{\rm CC} = 5.0 V$
VOL	Output Low Voltage		0.45	V	$I_{OL} = 2 mA$
VOH	Output High Voltage	2.4		V	I _{OH} = -400 μA
l _{IL}	Input Leakage		10	μΑ	$V_{SS} \le V_{IN} \le V_{CC}$
ILO	Output Leakage Current		±10	μA	$0.45V \le V_{OUT} \le V_{CC}$
ICC	V _{CC} Supply Current		180	mA	
IDD	V _{DD} Supply Current		30	mA	$V_{DD} = V_{CC}$
CIN	Capacitance of Input Buffer		10	pF	$f_{\rm C} = 1 \ \mu \text{Hz}$
C _{I/O}	Capacitance of I/O Buffer		15	pF	$f_{\rm C} = 1 \ \mu \text{Hz}$

D.C. CHARACTERISTICS—PROGRAMMING

 $T_A = 0^{\circ}C$ to 70°C, $V_{CC} = 5V \pm 5^{\circ}$, $V_{SS} = 0V$, $V_{DD} = 25V \pm 1V$

Symbol	Parameter	Min	Тур	Max	Unit
V _{DD}	Programming Voltage (during Write to EPROM)	24	25	26	V
IDD	Prog Supply Current		15	30	mA

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A.C. CHARACTERISTICS

 T_{A} = 0°C to 70°C, V_{CC} = 5V $\pm 5\%$

Symbol	Perameter	8755A		Helt
	Parameter	Min	Max	Unit
tcyc	Clock Cycle Time	320		ns
T ₁	CLK Pulse Width	80		ns
T ₂	CLK Pulse Width	120		ns
t _f , t _r	CLK Rise and Fall Time		30	ns
t _{AL}	Address to Latch Set Up Time	50		ns
t _{LA}	Address Hold Time after Latch	80		ns
t _{LC}	Latch to READ/WRITE Control	100		ns
t _{RD}	Valid Data Out Delay from READ Control*		170	ns
t _{AD}	Address Stable to Data Out Valid**		450	ns
tLL	Latch Enable Width	100		ns
tRDF	Data Bus Float after READ	0	100	ns
tCL	READ/WRITE Control to Latch Enable	20		ns
tcc	READ/WRITE Control Width	250		ns
tow	Data in Write Set Up Time	150		ns
twp	Data in Hold Time after WRITE	30		ns
twp	WRITE to Port Output		400	ns
tPR	Port Input Set Up Time	50		ns
t _{RP}	Port Input Hold Time to Control	50		ns
t _{RYH}	READY HOLD Time to Control	0	160	ns
tARY	ADDRESS (CE) to READY		160	ns
t _{RV}	Recovery Time between Controls	300		ns
tRDE	READ Control to Data Bus Enable	10		ns

NOTES:

 $C_{LOAD} = 150 \text{ pF.} \\ *Or T_{AD} - (T_{AL} + T_{LC}) \text{, whichever is greater.} \\ **Defines ALE to Data Out Valid in conjunction with T_{AL}.$

A.C. CHARACTERISTICS-PROGRAMMING

 T_{A} = 0°C to 70°C, V_{CC} = 5V ±5%, V_{SS} = 0V, V_{DD} = 25V ±1V

Symbol	Parameter	Min	Тур	Max	Unit
t _{PS}	Data Setup Time	10			ns
t _{PD}	Data Hold Time	0			ns
ts	Prog Pulse Setup Time	2			μs
t _H	Prog Pulse Hold Time	2			μs
tPR	Prog Pulse Rise Time	0.01	2		μs
tPF	Prog Pulse Fall Time	0.01	2		μs
tPRG	Prog Pulse Width	45	50		ms

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A.C. TESTING INPUT, OUTPUT WAVEFORM



WAVEFORMS

CLOCK SPECIFICATION FOR 8755A





PROM READ, I/O READ AND WRITE



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8755A

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WAVEFORMS (Continued)

I/O PORT



WAIT STATE (READY = 0)



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WAVEFORMS (Continued)

8755A PROGRAM MODE

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